

Features

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Design for inverter supply application

品名 : FH2608TN		
$I_{T(AV)}$	2608A	
V_{DRM}	2000V~3000V	
V_{RRM}	1000V~2500V	
t_q	20~75μs	



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, $T_c=55^\circ C$	125			2608	A
						2206	
V_{DRM}	Repetitive peak off-state voltage	tp=10ms	125	2000		3000	V
				1000		2500	
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			200	mA
I_{TSM}	Surge on-state current	10ms half sine wave $V_R=0.6V_{RRM}$	125			28	kA
						3920	
V_{TO}	Threshold voltage		125			1.21	V
						0.16	
V_{TM}	Peak on-state voltage	$I_{TM}=4000A$, $F=32kN$	25	20≤ t_q ≤45		2.60	V
				46≤ t_q ≤60		2.40	
				61≤ t_q ≤75		2.20	
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ to 3000A Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=1.5A$	125			1500	A/μs
Q_{rr}	Recovery charge	$I_{TM}=2000A$, tp=4000μs, $di/dt=-20A/\mu s$, $V_R=100V$	125		1200		μC
t_q	Circuit commutated turn-off time	$I_{TM}=2000A$, tp=4000μs, $V_R=100V$ $dv/dt=30V/\mu s$, $di/dt=-20A/\mu s$	100	20		75	μs
I_{GT} V_{GT} I_H I_L		$V_A=12V$, $I_A=1A$	25	45		300	mA
				0.9		4.5	
				20		500	
						1000	
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	DC double side cooled				0.012	°C /W
						0.003	
F_m	Mounting force			30		40	kN
T_{vj}	Junction temperature			-40		125	°C
T_{stg}	Stored temperature			-40		140	°C
W_t	Weight				880		g
Outline			P15				

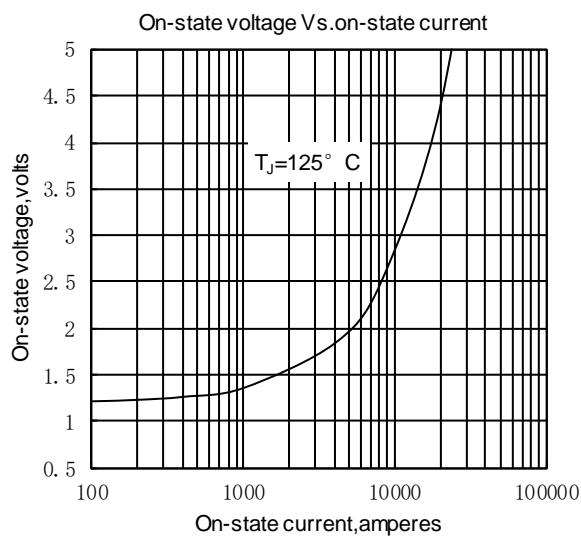


Fig.1

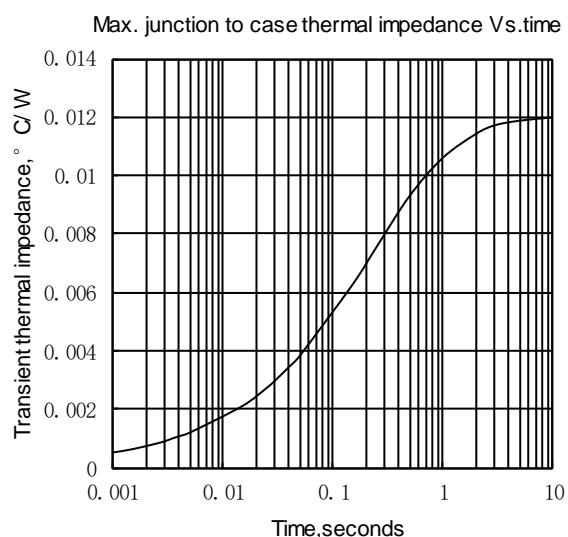


Fig.2

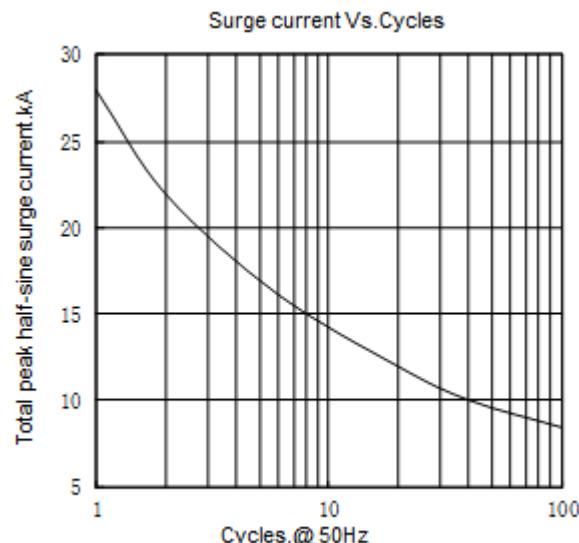


Fig.3

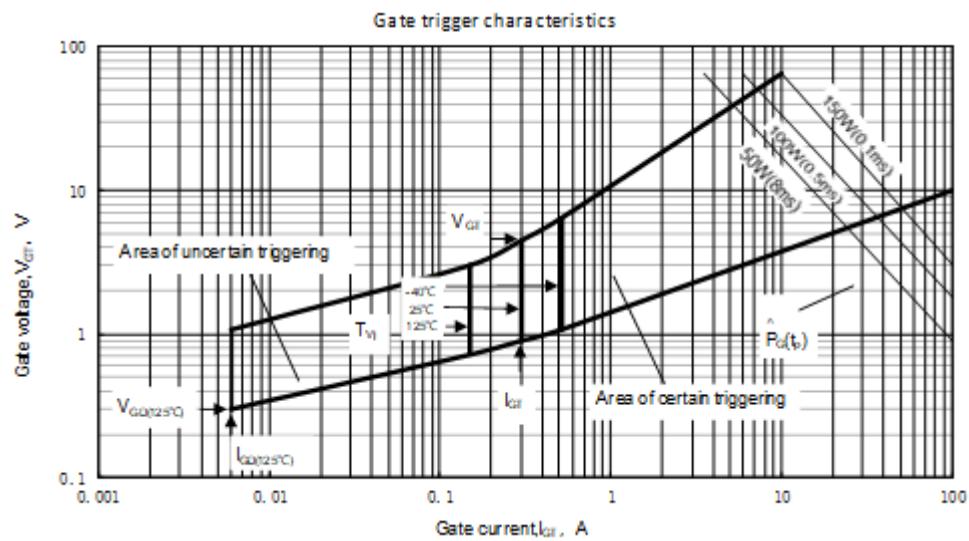


Fig.4

